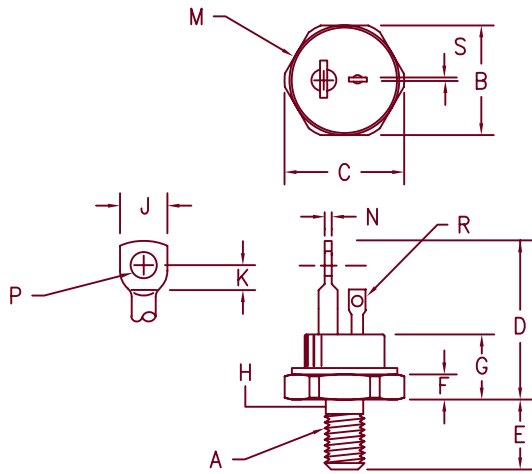


Silicon Controlled Rectifier/Inverter Series 035



Dim.	Inches		Millimeter		Notes
	Minimum	Maximum	Minimum	Maximum	
A	---	---	---	---	1
B	.677	.685	17.20	17.40	
C	---	.770	---	19.56	
D	1.200	1.250	30.48	31.75	
E	.427	.447	10.84	11.35	
F	.115	.155	2.92	3.94	
G	---	.515	---	13.08	
H	---	.249	---	6.32	2
J	.200	.300	5.08	7.62	
K	.120	---	3.05	---	
M	---	.667	---	16.94	Dia.
N	.065	.085	1.65	2.15	
P	.145	.155	3.68	3.93	Dia.
R	.055	.065	1.40	1.65	Dia.
S	.025	.030	.64	.76	

Note 1: 1/4-28 UNF-3A

Note 2: Full thread within 2 1/2 threads

TO-208AC (TO-65)

Microsemi Catalog Number	Forward & Reverse Repetitive Blocking VDRM, VRRM
03508G(2)F	800V
03510G(2)F	1000V
03512G(2)F	1200V

Note 1: To specify dv/dt other than 200V/usec., enter appropriate letter in place of "G":
 K 300V/usec.
 H 500V/usec.
 J 1000V/usec.

Note 2: To specify tq, enter appropriate letter in (2)
 W-30 usec
 X-40 usec

- dv/dt-200 V/usec
- 1000 amperes surge current
- Low forward on-state voltage
- Blocking voltages up to 1200 volts
- Primarily for forced commutated applications

Electrical Characteristics		
Max. RMS on-state current	$I_T(\text{RMS})$ 63 Amps	$T_C = 100^\circ\text{C}$, half sine wave, $R_{\theta JC} = 0.35^\circ\text{C/W}$
Max. average on-state cur.	$I_T(\text{AV})$ 40 Amps	$T_C = 100^\circ\text{C}$, half sine wave, $R_{\theta JC} = 0.35^\circ\text{C/W}$
Max. peak on-state voltage	V_{TM} 2.8 Volts	$I_{TM} = 120 \text{ A(peak)}$
Max. holding current	I_H 500 mA	
Max. peak one cycle surge current	I_{TSM} 800 A	$T_C = 100^\circ\text{C}$, 60Hz
Max. I^2t capability for fusing	I^2t 2650A ² S	$t = 8.3 \text{ ms}$
$T_C = 25^\circ\text{C}$ unless otherwise noted		

Thermal and Mechanical Characteristics		
Operating junction temp range	T_J	-65°C to 125°C
Storage temperature range	T_{STG}	-65°C to 150°C
Maximum thermal resistance	$R_{\theta JC}$	0.35°C/W Junction to case
Typical thermal resistance (greased)	$R_{\theta CS}$	0.20°C/W Case to sink
Mounting torque		25-30 inch pounds
Weight		0.56 ounces (16 grams) typical



6 Lake Street
 Lawrence, MA 01841
 PH: (978) 620-2600
 FAX: (978) 689-0803
www.microsemi.com

04-24-07 Rev. 2

035

Switching

Critical rate of rise of on-state current (note 1)	di/dt	200A/usec.	$T_J = 125^\circ\text{C}$
Typical delay time (note 1)	t_d	2.0 usec.	
Maximum circuit commuted turn-off time (note 2)	t_q (W)	30 usec.	$T_J = 125^\circ\text{C}$
	t_q (X)	40 usec.	$T_J = 125^\circ\text{C}$

Note 1: $I_{TM} = 50\text{A}$, $V_D = V_{DRM}$, $V_{GT} = 12\text{V}$ open circuit, 20 ohm-0.1 usec. rise time

Note 2: $I_{TM} = 50\text{A}$, $di/dt = -5\text{A/usec.}$, V_R during turn-off interval = 50V min.,
reapplied $dv/dt = 20\text{V/usec.}$, $V_{GT} = 0\text{V}$

Triggering

Max. gate voltage to trigger	V_{GT}	2.0V	$T_J = 25^\circ\text{C}$
Max. nontriggering gate voltage	V_{GD}	0.15V	$T_J = 125^\circ\text{C}$
Max. gate current to trigger	I_{GT}	150mA	$T_J = 25^\circ\text{C}$
Max. peak gate power	P_{GM}	10W	
Average gate power	$P_{G(AV)}$	2.0W	$t_p = 10$ usec.
Max. peak gate current	I_{GM}	3.0A	
Max. peak gate voltage (forward)	V_{GM}	20V	
Max. peak gate voltage (reverse)	V_{GM}	10V	

Blocking

Max. leakage current	I_{RRM}, I_{DRM}	20mA	$T_J = 125^\circ\text{C} \ \& \ V_{DRM}, V_{RRM}$
Max. reverse leakage	I_{RRM}, I_{DRM}	500 μA	$T_J = 25^\circ\text{C} \ \& \ V_{RRM}, V_{DRM}$
Critical rate of rise of off-state voltage	dv/dt	200V/usec.	$T_J = 125^\circ\text{C}$

Figure 1
Typical Forward On-State Characteristics

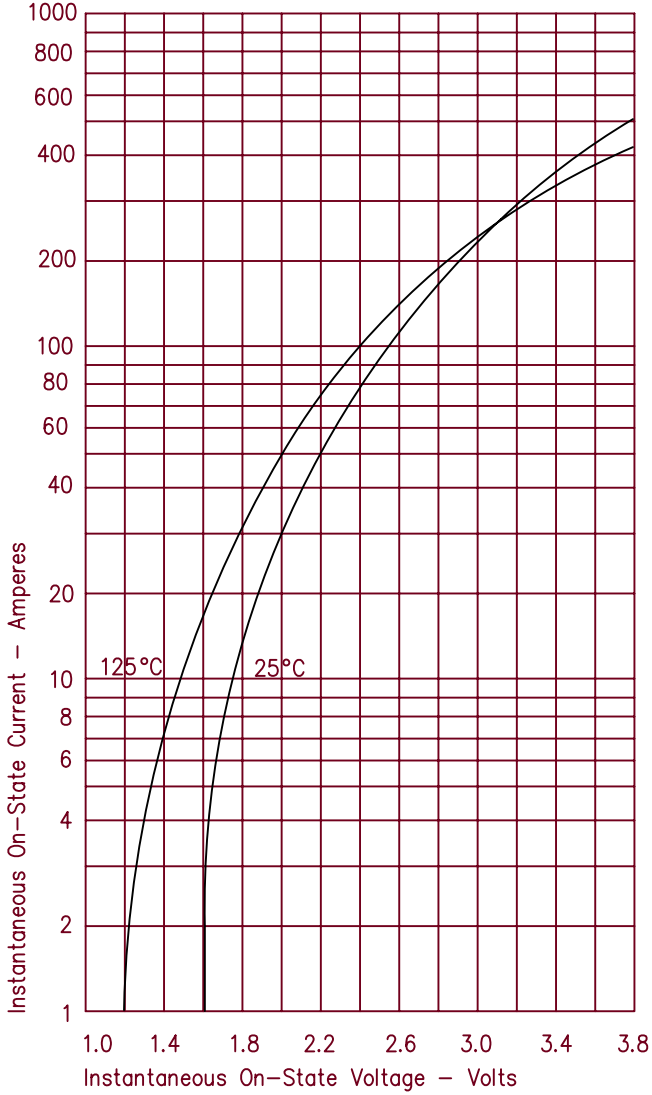


Figure 3
Maximum Power Dissipation

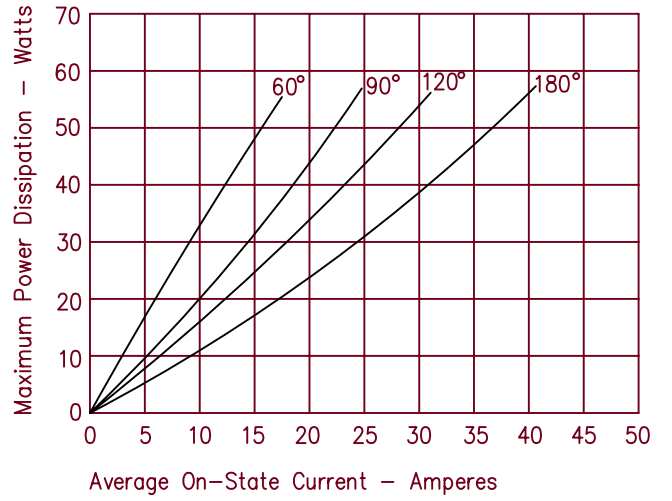


Figure 4
Transient Thermal Impedance

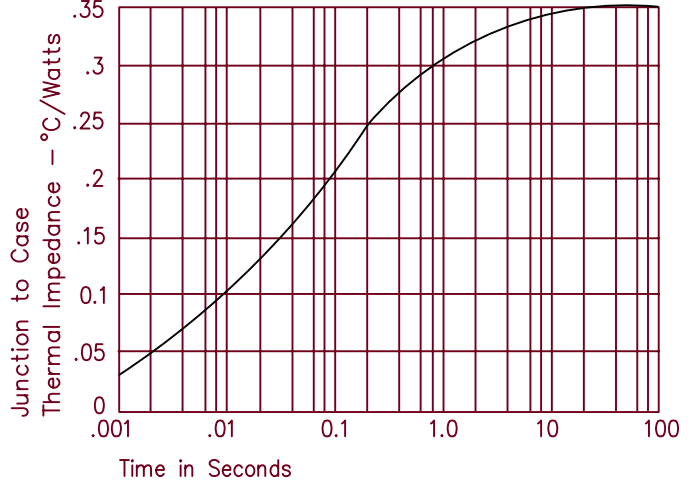


Figure 2
Forward Current Derating

